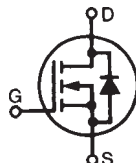


**GigaMOS™**  
**Power MOSFET**
**IXFK160N30T**  
**IXFX160N30T**

 N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode


$$V_{DSS} = 300V$$

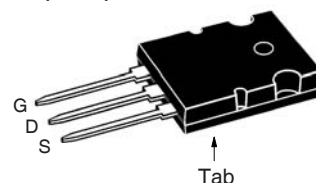
$$I_{D25} = 160A$$

$$R_{DS(on)} \leq 19m\Omega$$

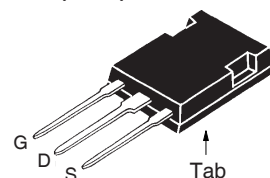
$$t_{rr} \leq 200ns$$

| Symbol        | Test Conditions  | Maximum Ratings   |            |
|---------------|--|-------------------|------------|
| $V_{DSS}$     | $T_J = 25^\circ C$ to $150^\circ C$                                | 300               | V          |
| $V_{DGR}$     | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$          | 300               | V          |
| $V_{GSS}$     | Continuous   | $\pm 20$          | V          |
| $V_{GSM}$     | Transient  | $\pm 30$          | V          |
| $I_{D25}$     | $T_C = 25^\circ C$   | 160               | A          |
| $I_{DM}$      | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 440               | A          |
| $I_A$         | $T_C = 25^\circ C$   | 80                | A          |
| $E_{AS}$      | $T_C = 25^\circ C$   | 5                 | J          |
| $dV/dt$       | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$ | 20                | V/ns       |
| $P_D$         | $T_C = 25^\circ C$   | 1390              | W          |
| $T_J$         |  | -55 ... +150      | $^\circ C$ |
| $T_{JM}$      |  | 150               | $^\circ C$ |
| $T_{stg}$     |  | -55 ... +150      | $^\circ C$ |
| $T_L$         | Maximum Lead Temperature for Soldering                             | 300               | $^\circ C$ |
| $T_{SOLD}$    | Plastic Body for 10s   | 260               | $^\circ C$ |
| $M_d$         | Mounting Torque (TO-264)   | 1.13/10           | Nm/lb.in   |
| $F_c$         | Mounting Force (PLUS247)   | 20..120 / 4.5..27 | N/lb       |
| <b>Weight</b> | TO-264   | 10                | g          |
|               | PLUS247  | 6                 | g          |

TO-264 (IXFK)



PLUS247 (IXFX)


 G = Gate      D = Drain  
 S = Source      Tab = Drain

**Features**

- International Standard Packages
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values |      |                    |
|--------------|---|-----------------------|------|--------------------|
|              |   | Min.                  | Typ. | Max.               |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 3mA$   | 300                   |      | V                  |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 8mA$                                     | 3.0                   |      | 5.0 V              |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                  |                       |      | $\pm 200$ nA       |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ C$           |                       |      | 50 $\mu A$<br>3 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 80A$ , Note 1                               |                       |      | 19 m $\Omega$      |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)  | Characteristic Values |      |                        |
|--------------|--|-----------------------|------|------------------------|
|              |  | Min.                  | Typ. | Max.                   |
| $g_{fs}$     | $V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1   | 90                    | 150  | S                      |
| $C_{iss}$    | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$   |                       | 24.5 | nF                     |
| $C_{oss}$    |  |                       | 1825 | pF                     |
| $C_{rss}$    |  |                       | 45   | pF                     |
| $R_{Gi}$     | Gate Input Resistance  |                       | 1.1  | $\Omega$               |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 15\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\Omega$ (External) |                       | 34   | ns                     |
| $t_r$        |  |                       | 68   | ns                     |
| $t_{d(off)}$ |  |                       | 90   | ns                     |
| $t_f$        |  |                       | 23   | ns                     |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$   |                       | 376  | nC                     |
| $Q_{gs}$     |  |                       | 140  | nC                     |
| $Q_{gd}$     |  |                       | 56   | nC                     |
| $R_{thJC}$   |  |                       |      | $0.09^\circ\text{C/W}$ |
| $R_{thCS}$   |  | 0.15                  |      | $^\circ\text{C/W}$     |

### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                    | Characteristic Values |      |               |
|----------|--|-----------------------|------|---------------|
|          |  | Min.                  | Typ. | Max.          |
| $I_S$    | $V_{GS} = 0\text{V}$   |                       |      | 160 A         |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$  |                       |      | 640 A         |
| $V_{SD}$ | $I_F = 60\text{A}, V_{GS} = 0\text{V}$ , Note 1  |                       |      | 1.4 V         |
| $t_{rr}$ | $I_F = 80\text{A}, -di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 75\text{V}, V_{GS} = 0\text{V}$ |                       |      | 200 ns        |
| $Q_{RM}$ |  |                       | 1.09 | $\mu\text{C}$ |
| $I_{RM}$ |  |                       | 13   | A             |

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

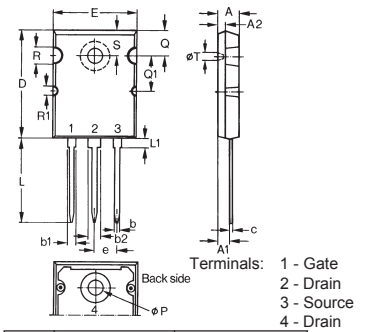
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

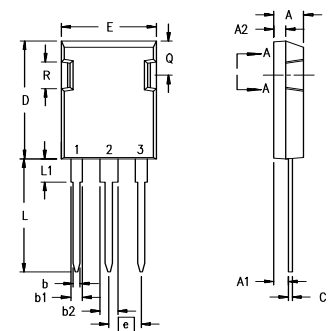
IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

### TO-264 AA Outline



| Dim. | Millimeter |       | Inches   |       |
|------|------------|-------|----------|-------|
|      | Min.       | Max.  | Min.     | Max.  |
| A    | 4.82       | 5.13  | .190     | .202  |
| A1   | 2.54       | 2.89  | .100     | .114  |
| A2   | 2.00       | 2.10  | .079     | .083  |
| b    | 1.12       | 1.42  | .044     | .056  |
| b1   | 2.39       | 2.69  | .094     | .106  |
| b2   | 2.90       | 3.09  | .114     | .122  |
| c    | 0.53       | 0.83  | .021     | .033  |
| D    | 25.91      | 26.16 | 1.020    | 1.030 |
| E    | 19.81      | 19.96 | .780     | .786  |
| e    | 5.46 BSC   |       | .215 BSC |       |
| J    | 0.00       | 0.25  | .000     | .010  |
| K    | 0.00       | 0.25  | .000     | .010  |
| L    | 20.32      | 20.83 | .800     | .820  |
| L1   | 2.29       | 2.59  | .090     | .102  |
| P    | 3.17       | 3.66  | .125     | .144  |
| Q    | 6.07       | 6.27  | .239     | .247  |
| Q1   | 8.38       | 8.69  | .330     | .342  |
| R    | 3.81       | 4.32  | .150     | .170  |
| R1   | 1.78       | 2.29  | .070     | .090  |
| S    | 6.04       | 6.30  | .238     | .248  |
| T    | 1.57       | 1.83  | .062     | .072  |

### PLUS 247™ Outline



Terminals: 1 - Gate  
2 - Drain  
3 - Source

| Dim. | Millimeter |       | Inches   |       |
|------|------------|-------|----------|-------|
|      | Min.       | Max.  | Min.     | Max.  |
| A    | 4.83       | 5.21  | .190     | .205  |
| A1   | 2.29       | 2.54  | .090     | .100  |
| A2   | 1.91       | 2.16  | .075     | .085  |
| b    | 1.14       | 1.40  | .045     | .055  |
| b1   | 1.91       | 2.13  | .075     | .084  |
| b2   | 2.92       | 3.12  | .115     | .123  |
| C    | 0.61       | 0.80  | .024     | .031  |
| D    | 20.80      | 21.34 | .819     | .840  |
| E    | 15.75      | 16.13 | .620     | .635  |
| e    | 5.45 BSC   |       | .215 BSC |       |
| L    | 19.81      | 20.32 | .780     | .800  |
| L1   | 3.81       | 4.32  | .150     | .170  |
| Q    | 5.59       | 6.20  | .220     | 0.244 |
| R    | 4.32       | 4.83  | .170     | .190  |

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

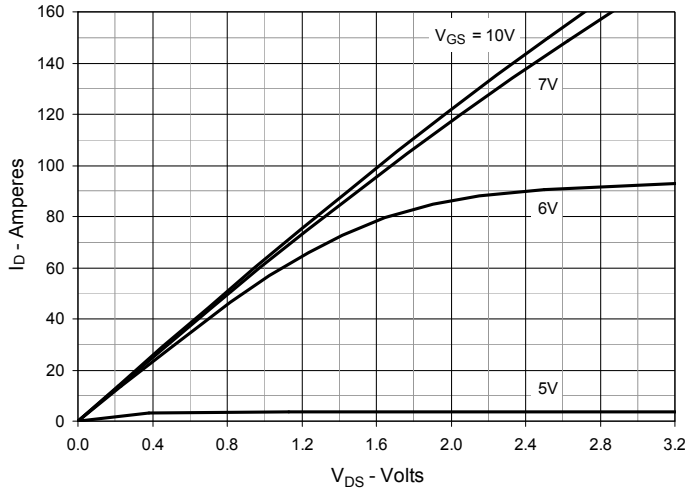


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

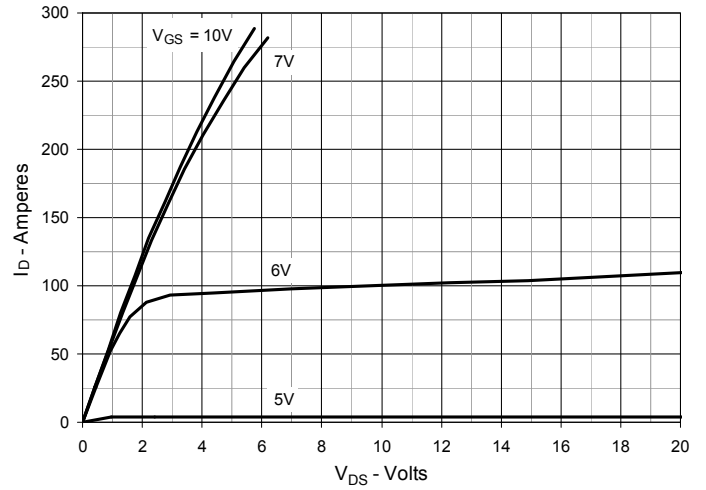


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

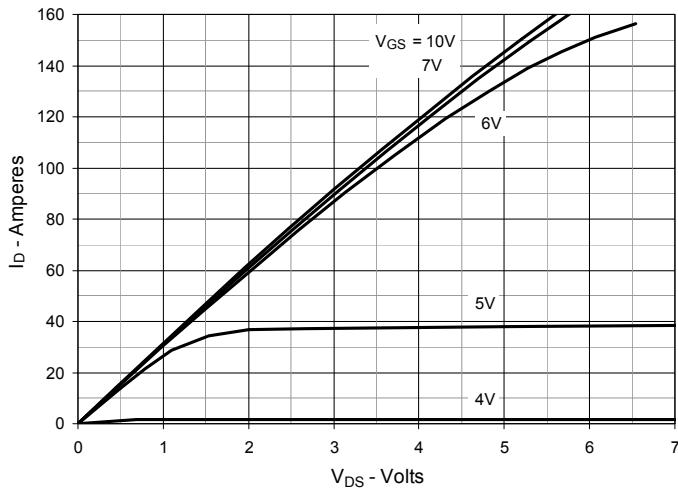


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 80\text{A}$  Value vs. Junction Temperature

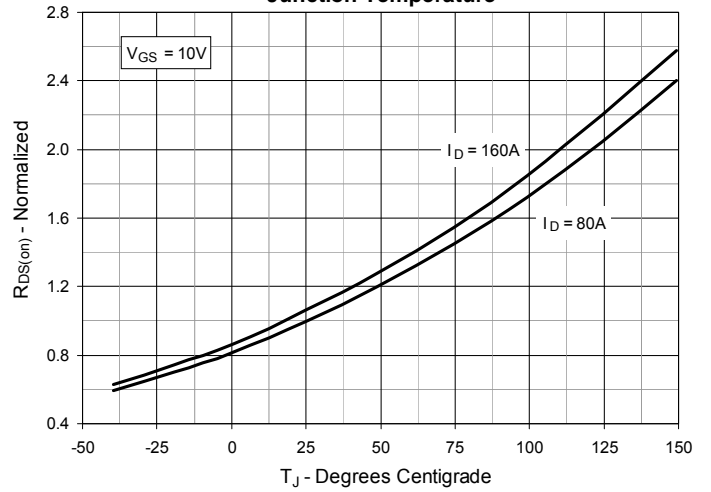


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 80\text{A}$  Value vs. Drain Current

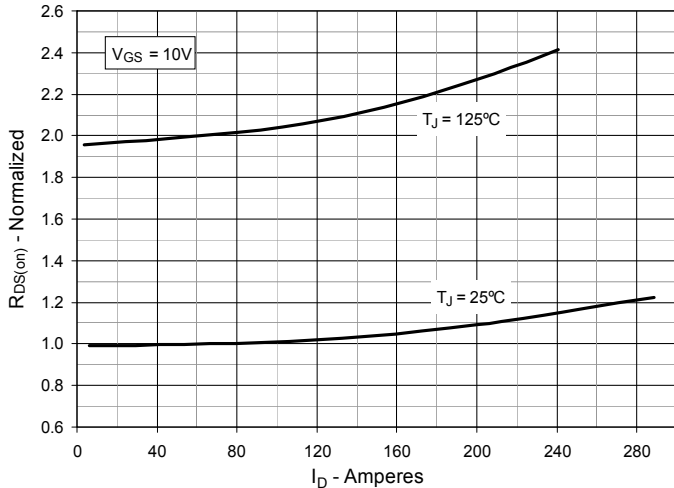
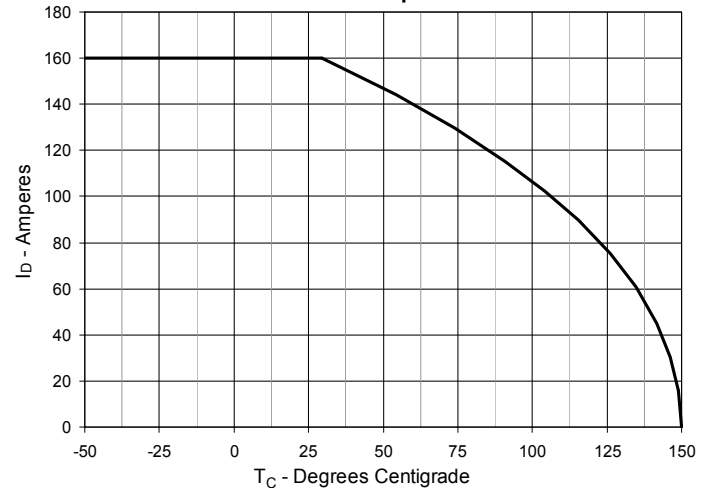
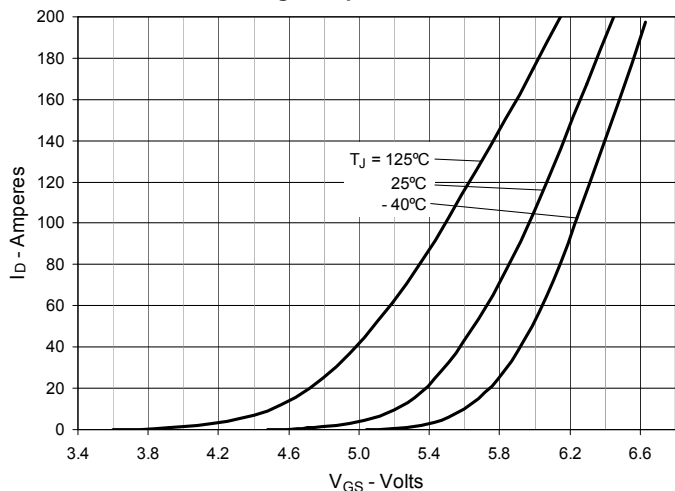


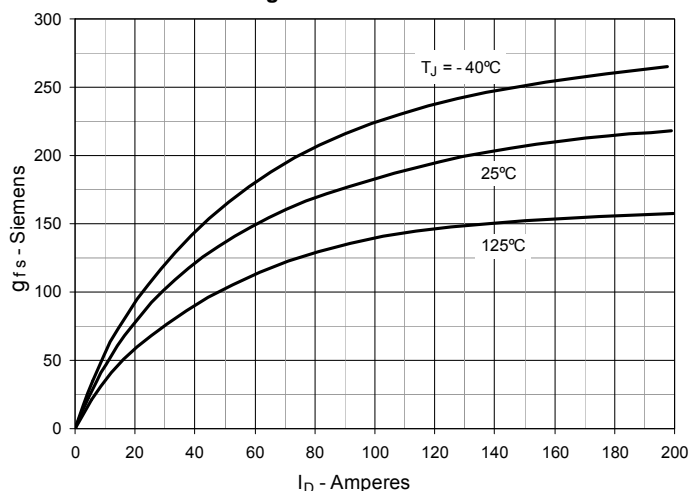
Fig. 6. Maximum Drain Current vs. Case Temperature



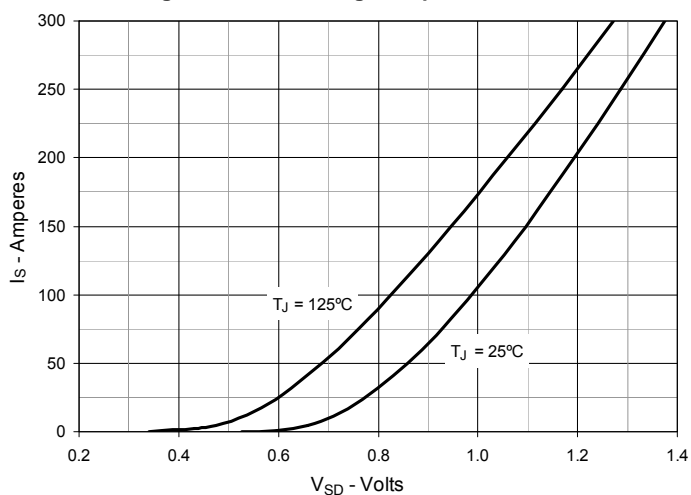
**Fig. 7. Input Admittance**



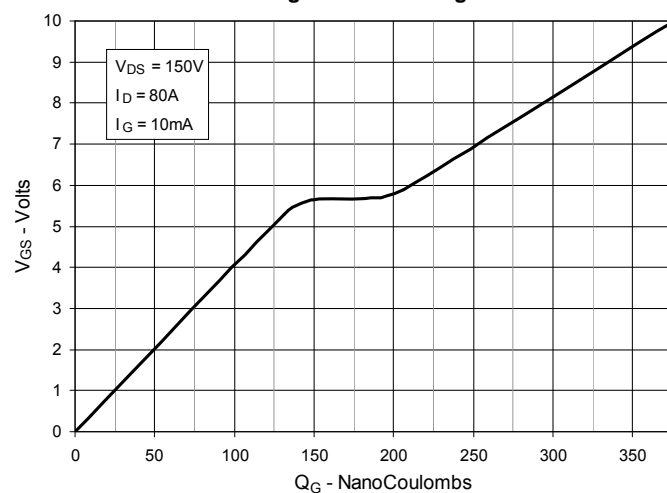
**Fig. 8. Transconductance**



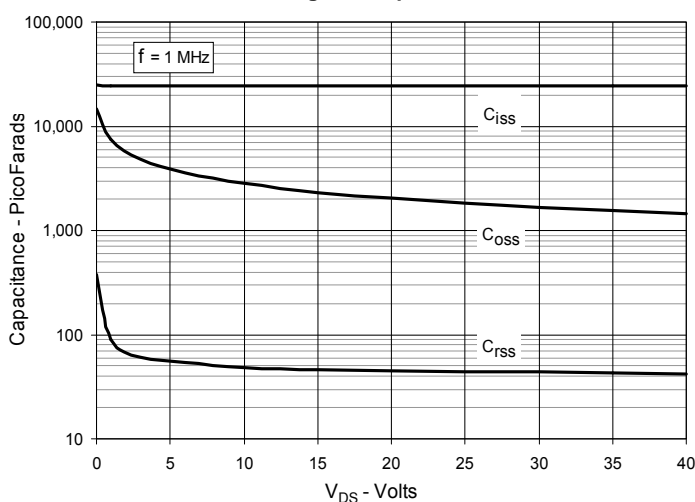
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



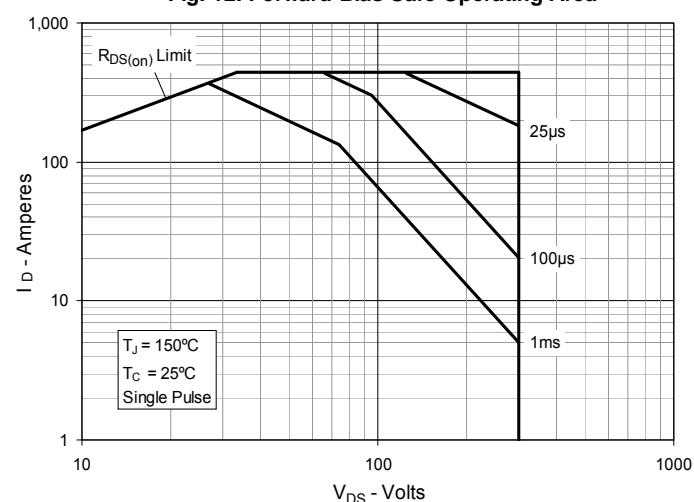
**Fig. 10. Gate Charge**



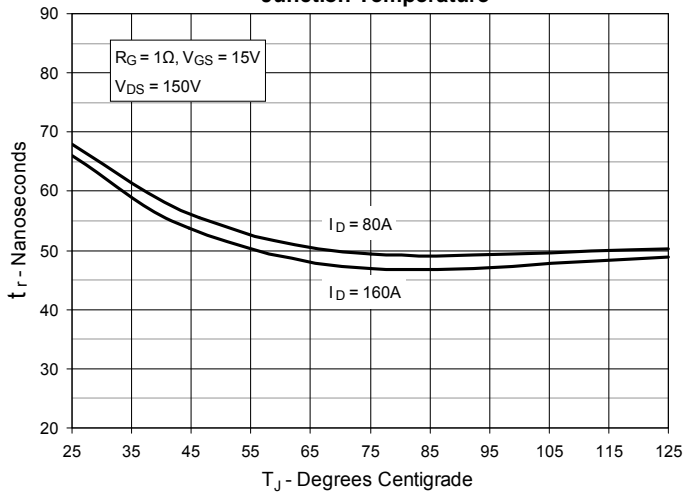
**Fig. 11. Capacitance**



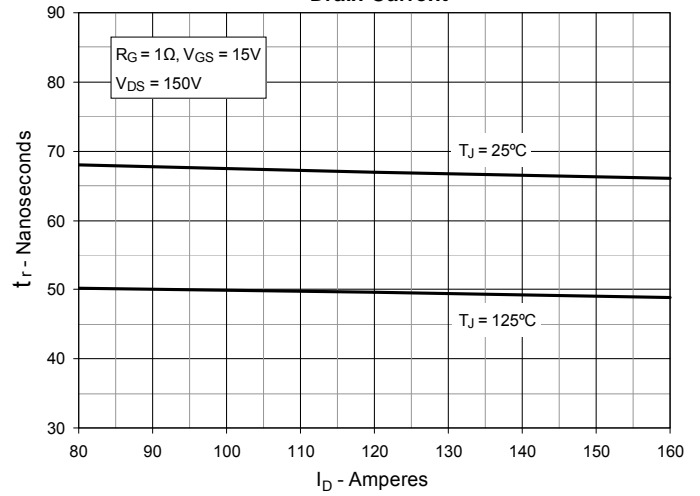
**Fig. 12. Forward-Bias Safe Operating Area**



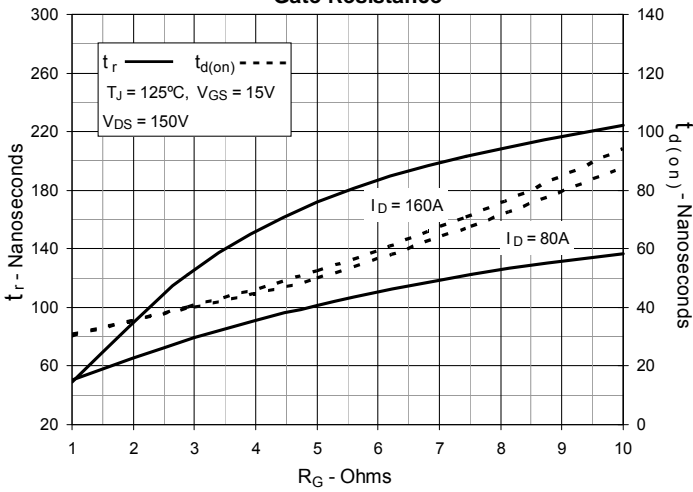
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



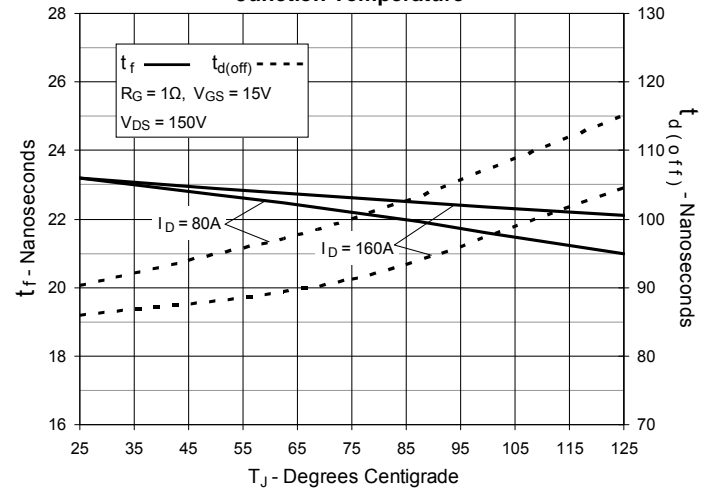
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



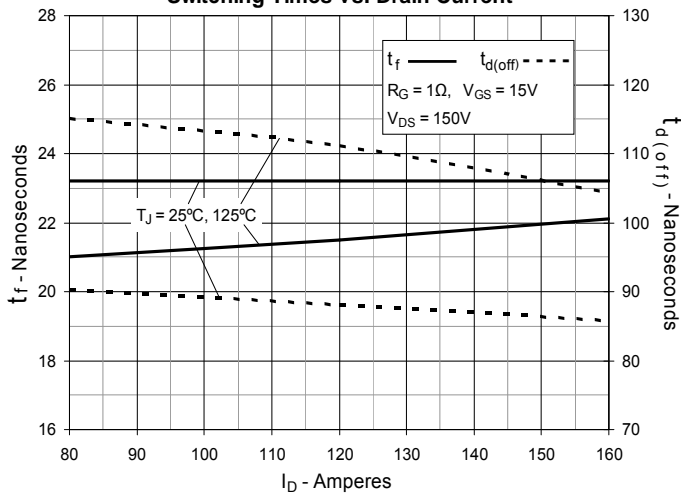
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

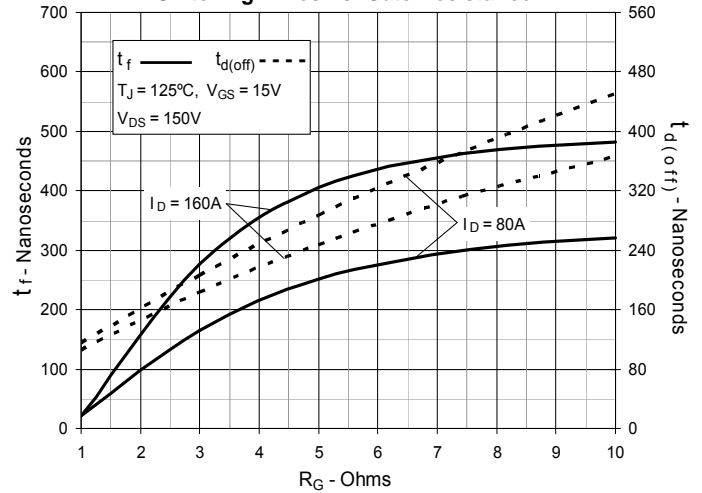
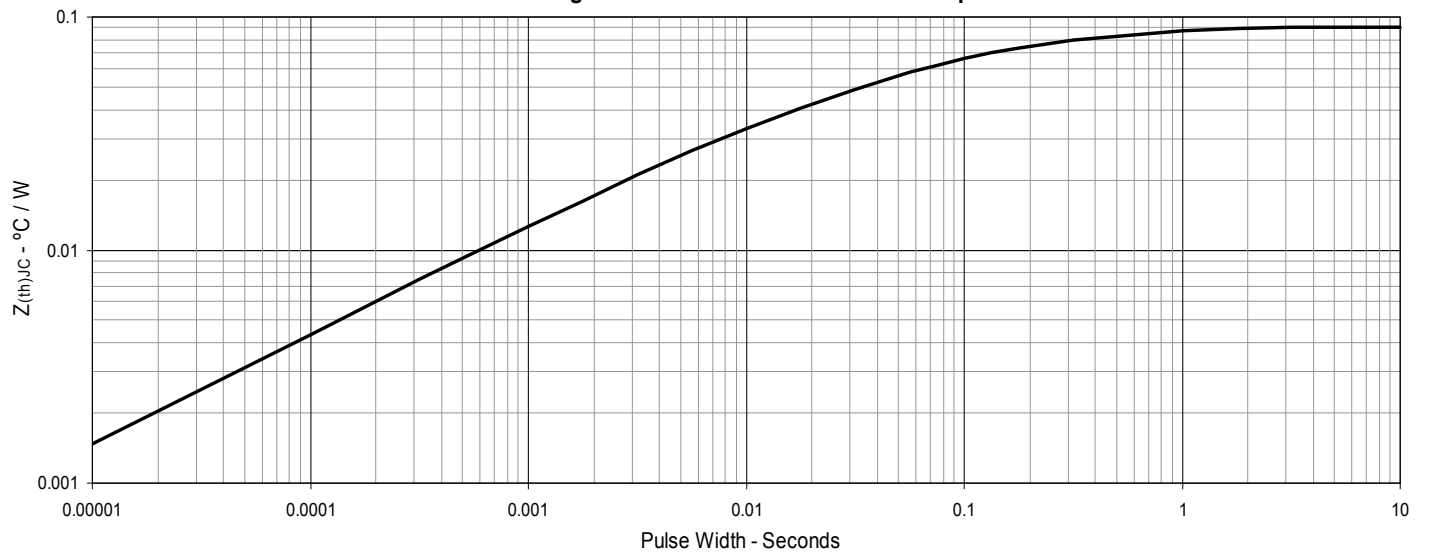


Fig. 19. Maximum Transient Thermal Impedance





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